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IR2122(S)

CURRENT SENSING SINGLE CHANNEL DRIVER

Features

- Floating channel designed for bootstrap operation
Fully operational to +600V
Tolerant to negative transient voltage
dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout
- 3.3V, 5V and 15V input logic compatible
- FAULT lead indicates shutdown has occurred
- Output out of phase with input

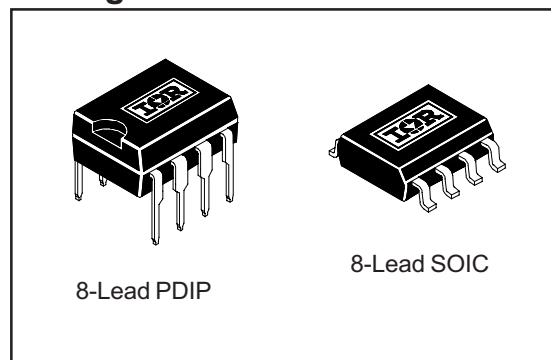
Description

The IR2122(S) is a high voltage, high speed power MOSFET and IGBT driver. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL outputs, down to 3.3V. The protection circuitry detects over-current in the driven power transistor and terminates the gate drive voltage. An open drain FAULT signal is provided to indicate that an over-current shutdown has occurred. The output driver features a high pulse current buffer stage designed for minimum cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side or low side configuration which operates up to 600 volts.

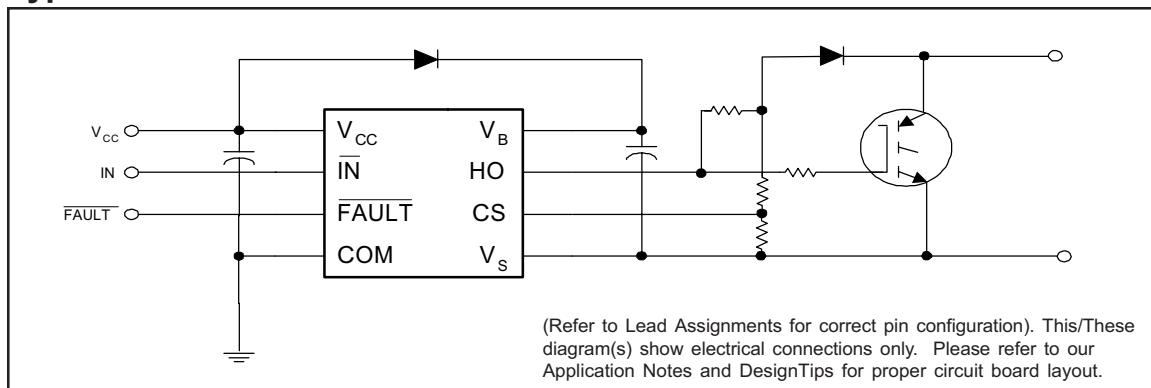
Product Summary

V_{OFFSET}	600V max.
I_{O+/-}	110 mA / 110 mA
V_{OUT}	10 - 20V
V_{CSth}	500 mV
t_{on/off} (typ.)	250 & 200 ns

Packages



Typical Connection



Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units
V_B	High Side Floating Supply Voltage	-0.3	625	V
V_S	High Side Floating Offset Voltage	$V_B - 25$	$V_B + 0.3$	
V_{HO}	High Side Floating Output Voltage	$V_S - 0.3$	$V_B + 0.3$	
V_{CC}	Logic Supply Voltage	-0.3	25	
V_{IN}	Logic Input Voltage	-0.3	$V_{CC} + 0.3$	
V_{FLT}	FAULT Output Voltage	-0.3	$V_{CC} + 0.3$	
V_{CS}	Current Sense Voltage	$V_S - 0.3$	$V_B + 0.3$	
dV_S/dt	Allowable Offset Supply Voltage Transient	—	50	V/ns
P_D	Package Power Dissipation @ $T_A \leq +25^\circ\text{C}$ (8 Lead DIP)	—	1.0	W
	(8 Lead SOIC)	—	0.625	
R_{THJA}	Thermal Resistance, Junction to Ambient (8 Lead DIP)	—	125	$^\circ\text{C}/\text{W}$
	(8 Lead SOIC)	—	200	
T_J	Junction Temperature	—	150	$^\circ\text{C}$
T_S	Storage Temperature	-55	150	
T_L	Lead Temperature (Soldering, 10 seconds)	—	300	

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. The V_S offset rating is tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
V_B	High Side Floating Supply Voltage	$V_S + 13$	$V_S + 20$	V
V_S	High Side Floating Offset Voltage	Note 1	600	
V_{HO}	High Side Floating Output Voltage	V_S	V_B	
V_{CC}	Logic Supply Voltage	13	20	
V_{IN}	Logic Input Voltage	0	V_{CC}	
V_{FLT}	FAULT Output Voltage	0	V_{CC}	
V_{CS}	Current Sense Signal Voltage	V_S	$V_S + 5$	
T_A	Ambient Temperature	-40	150	$^\circ\text{C}$

Note 1: Logic operational for V_S of -5 to +600V. Logic state held for V_S of -5V to $-V_{BS}$. (Please refer to the Design Tip DT97-3 for more details).

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC} , V_{BS}) = 15V, C_L = 1000 pF and T_A = 25°C unless otherwise specified. The dynamic electrical characteristics are measured using the test circuit shown in Figure 3.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
t_{on}	Turn-On Propagation Delay	—	250	—	ns	$V_S = 0V$
t_{off}	Turn-Off Propagation Delay	—	200	—		$V_S = 600V$
t_r	Turn-On Rise Time	—	250	—		$C_L = 1000\text{ pF}$
t_f	Turn-Off Fall Time	—	250	—		$C_L = 1000\text{ pF}$
t_{bl}	Start-Up Blanking Time	500	900	—		
t_{cs}	CS Shutdown Propagation Delay	—	350	—		
t_{fit}	CS to FAULT Pull-Up Propagation Delay	—	450	—		

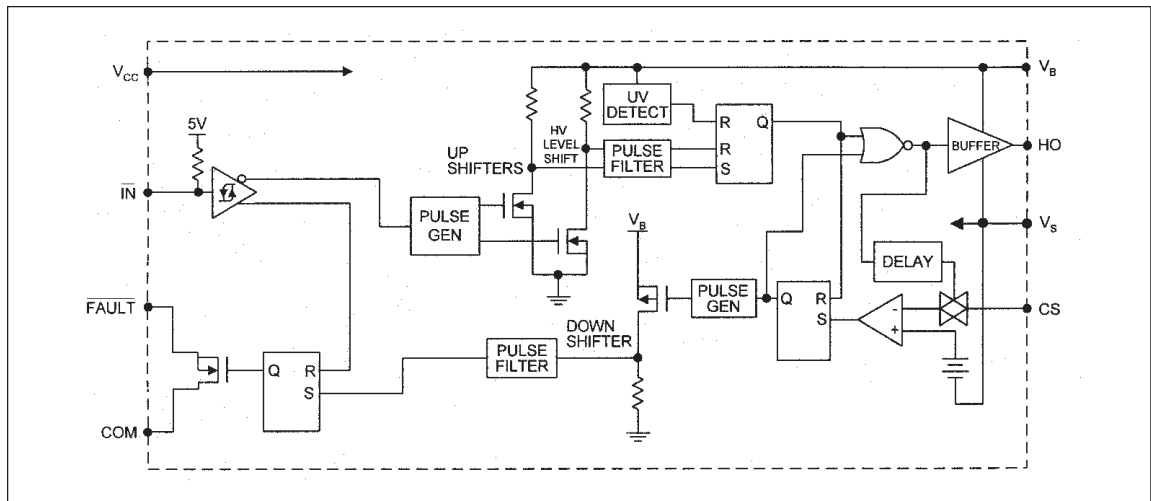
Static Electrical Characteristics

V_{BIAS} (V_{CC} , V_{BS}) = 15V and T_A = 25°C unless otherwise specified. The V_{IN} , V_{TH} and I_{IN} parameters are referenced to COM. The V_O and I_O parameters are referenced to V_S .

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
V_{IH}	Logic "0" Input Voltage (OUT = LO)	3.0	—	—	V	$V_{CC} = 10V \text{ to } 20V$
V_{IL}	Logic "1" Input Voltage (OUT = HI)	—	—	0.8		$V_{CC} = 10V \text{ to } 20V$
V_{CSTH+}	CS Input Positive Going Threshold	350	500	650	mV	$V_{CC} = 10V \text{ to } 20V$
V_{OH}	High Level Output Voltage, $V_{BIAS} - V_O$	—	—	100		$I_O = 0A$
V_{OL}	Low Level Output Voltage, V_O	—	—	100		$I_O = 0A$
I_{LK}	Offset Supply Leakage Current	—	—	50		$V_B = V_S = 600V$
I_{QBS}	Quiescent V_{BS} Supply Current	—	150	350	μA	$V_{IN} = 0V \text{ or } 5V$
I_{QCC}	Quiescent V_{CC} Supply Current	—	60	120		$V_{IN} = 0V \text{ or } 5V$
I_{IN+}	Logic "1" Input Bias Current	—	7.0	15		$V_{IN} = 0V$
I_{IN-}	Logic "0" Input Bias Current	—	—	1.0		$V_{IN} = 5V$
I_{CS+}	"High" CS Bias Current	—	—	1.0		$V_{CS} = 3V$
I_{CS-}	"High" CS Bias Current	—	—	1.0		$V_{CS} = 0V$
V_{BSUV+}	V_{BS} Supply Undervoltage Positive Going Threshold	10.0	11.4	13.0	V	
V_{BSUV-}	V_{BS} Supply Undervoltage Negative Going Threshold	9.5	10.4	12.5		
I_{O+}	Output High Short Circuit Pulsed Current	110	130	—	mA	$V_O = 0V, V_{IN} = 0V$ $PW \leq 10\text{ }\mu s$
I_{O-}	Output Low Short Circuit Pulsed Current	110	130	—		$V_O = 15V, V_{IN} = 5V$ $PW \leq 10\text{ }\mu s$

IR2122(S)

Functional Block Diagram



Lead Definitions

Lead	
Symbol	Description
V _{CC}	Logic and gate drive supply
IN	Logic input for gate driver output (HO), out of phase with HO
FAULT	Indicates over-current shutdown has occurred, negative logic
COM	Logic ground
V _B	High side floating supply
HO	High side gate drive output
V _S	High side floatn
CS	Current sense input to current sense comparator

Lead Assignments

<p>8 Lead PDIP IR2122</p>	<p>8 Lead SOIC IR2122S</p>
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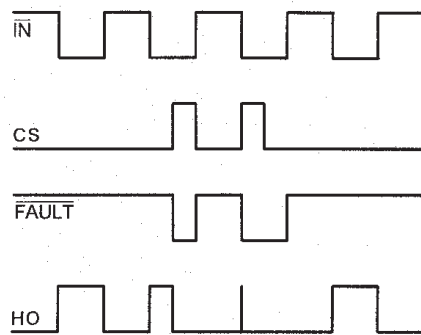


Figure 1. Input/Output Timing Diagram

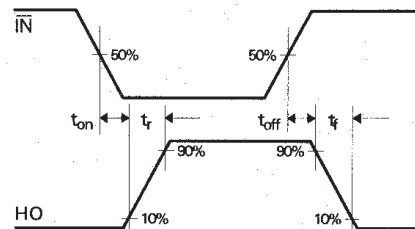


Figure 2. Switching Time Waveform Definition

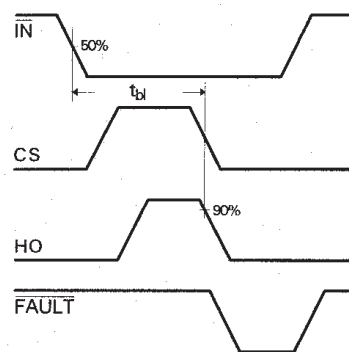


Figure 3. Start-up Blanking Time Waveform Definitions

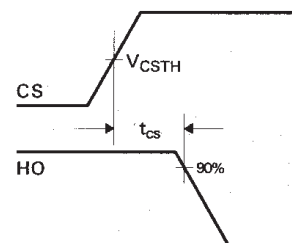


Figure 4. CS Shutdown Waveform Definitions

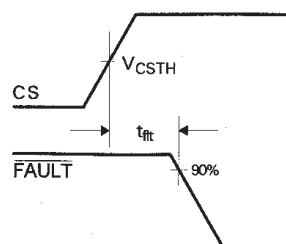
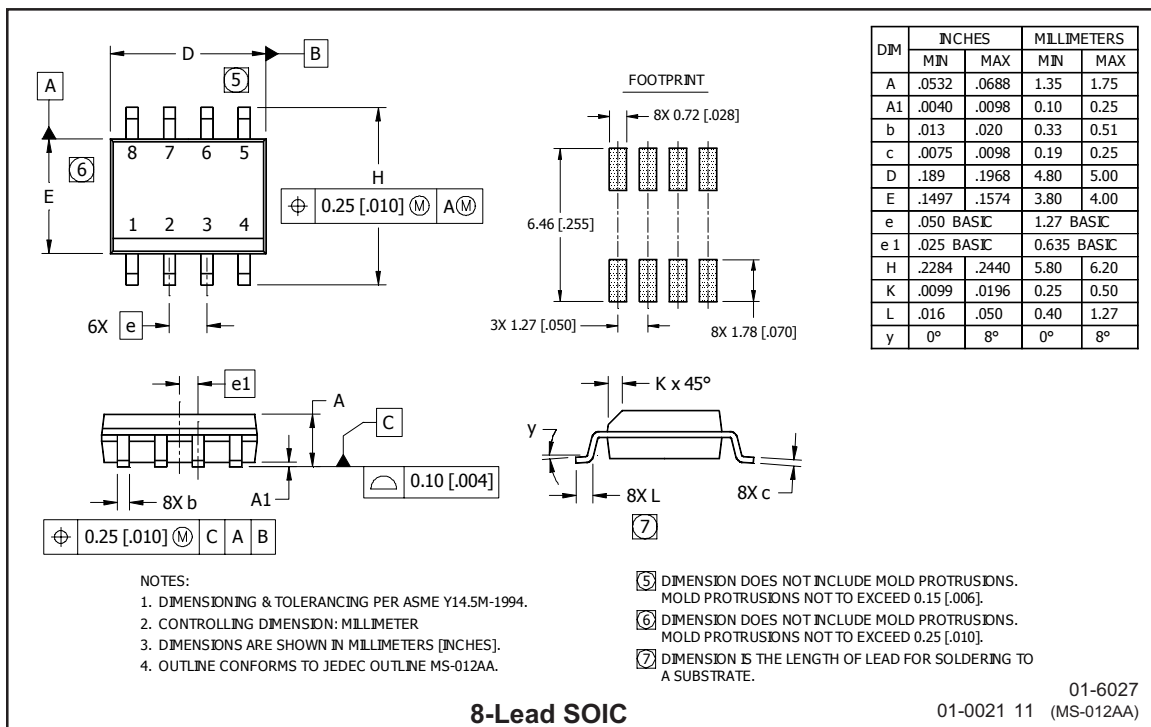
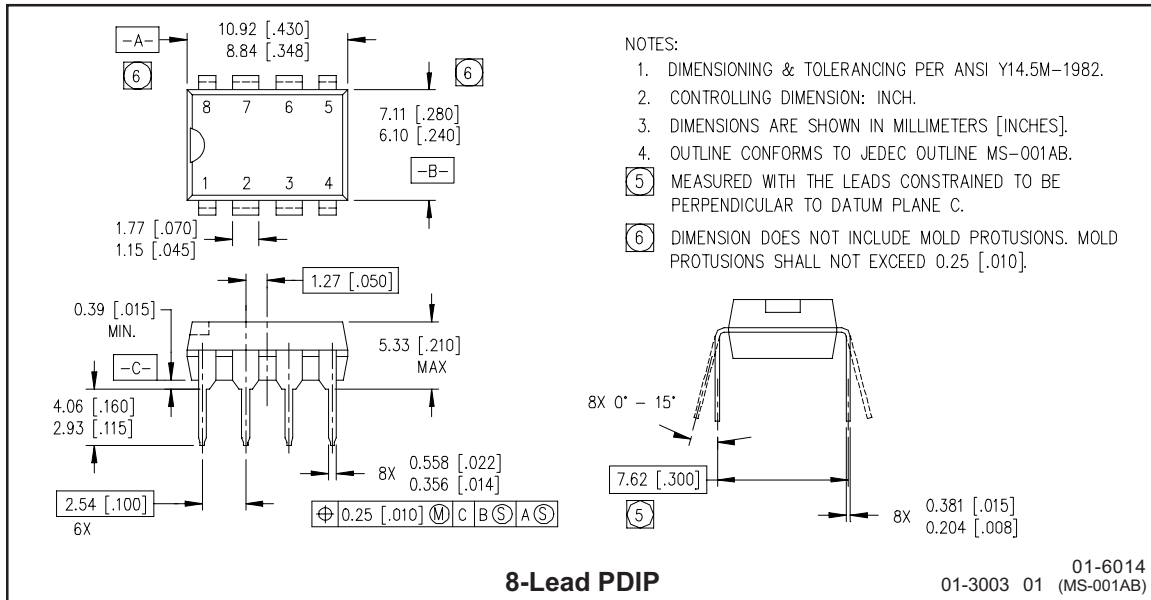


Figure 5. CS to $\overline{\text{FAULT}}$ Waveform Definitions

IR2122(S)

International
IR Rectifier

Case outlines



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Data and specifications subject to change without notice. 2/2/2005